

FDI040N06 N-Channel PowerTrench[®] MOSFET 60V, 168A, 4.0m Ω

Features

- $R_{DS(on)} = 3.2m\Omega$ (Typ.) @ $V_{GS} = 10V$, $I_D = 75A$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

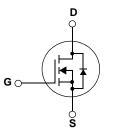
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

• DC to DC convertors / Synchronous Rectification





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol			FDI040N06	Units		
V _{DSS}	Drain to Source Voltage			60	V	
V _{GSS}	Gate to Source Voltage			±20	V	
ID	Drain Current	-Continuous (T _C = 25°C, Silicion	Limited)	168*		
		-Continuous (T _C = 100 ^o C, Silicion	n Limited)	118*	Α	
		-Continuous (T _C = 25°C, Packag	e Limited)	120		
I _{DM}	Drain Current	- Pulsed	- Pulsed (Note 1)		A	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			872	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)			7.0	V/ns	
P _D	Dawar Diasinatian	$(T_{\rm C} = 25^{\rm o}{\rm C})$		231	W	
	Power Dissipation	- Derate above 25°C		1.54	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C	
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C	

*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	FDI040N06	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max	0.65	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max	62.5	C/VV

August 2012

Device Marking FDI040N06		Device	Package	е	Reel Size	Таре	e Width		Quantit	v
		FDI040N06	TO-262	0		-		50		
Electrica	I Chara	acteristics T _c =	25°C unless o	otherwise no	ted			I		
Symbol		Parameter		Т	est Conditions	;	Min.	Тур.	Max.	Units
Off Charac	teristics	6		1		L. L			1	
BV _{DSS}	Drain to Source Breakdown Voltage			$I_D = 250 \mu A, V_{GS} = 0V, T_C = 25^{\circ}C$			60	-	-	V
ΔBV_{DSS} ΔT_J	Breakdown Voltage Temperature Coefficient		$I_D = 250 \mu A$, Referenced to $25^{\circ}C$			-	0.04	-	V/ºC	
	Zaro Cata Valtaga Drain Current		$V_{DS} = 60V, V_{GS} = 0V$		-	-	1	^		
IDSS	Zeio Ga	Zero Gate Voltage Drain Current		$V_{DS} = 60V, V_{GS} = 0V, T_{C} = 150^{\circ}C$		-	-	500	μA	
I _{GSS}	Gate to	Gate to Body Leakage Current			$V_{GS} = \pm 20V, V_{DS} = 0V$			-	±100	nA
On Charac	teristics	5								
V _{GS(th)}	Gate Threshold Voltage			$V_{GS} = V_{DS}, I_D = 250 \mu A$		2.5	3.5	4.5	V	
R _{DS(on)}		Static Drain to Source On Resistance		$V_{GS} = 10V, I_D = 75A$			-	3.2	4.0	mΩ
9FS	Forward	orward Transconductance		V _{DS} = 10V, I _D = 75A			-	169	-	S
Dynamic C	Input Ca	pacitance	V _{DS} = 25V, V _{GS} = 0V f = 1MHz		-	6190 900	8235 1195	pF pF		
C _{oss} C _{rss}		Transfer Capacitance			Hz	-	-	385	580	pF
Q _{g(tot)}		te Charge at 10V	·	V _{DS} = 48V, I _D = 75A V _{GS} = 10V (Note 4)		-	102	133	nC	
Q _{gs}		Source Gate Charge				-	32	-	nC	
Q _{gd}		Drain "Miller" Charge				-	32	-	nC	
Switching	Charact	eristics							I	
t _{d(on)}		Delay Time					-	30	70	ns
t _r	Turn-On	Rise Time			80V, I _D = 75A	-	40	90	ns	
t _{d(off)}	Turn-Off	Delay Time		V_{GS} = 10V, R_{GEN} = 4.7 Ω		F	-	55	120	ns
t _f	Turn-Off	Fall Time		(Note 4)			-	24	58	ns
Drain-Sou	rce Diod	e Characteristic	s			·				
I _S	Maximum Continuous Drain to Source Diode Forward Current					-	-	168	A	
I _{SM}	Maximum Pulsed Drain to Source Diode For			orward Current		-	-	672	Α	
V _{SD}	Drain to	Source Diode Forward	d Voltage	V _{GS} = 0V, I	_{SD} = 75A		-	-	1.3	V
t _{rr}	Reverse	Recovery Time		V _{GS} = 0V, 1	-		-	41	-	ns
Q _{rr}	Poveree	Recovery Charge		$dI_{\rm F}/dt = 100A/\mu s$			-	47	-	nC

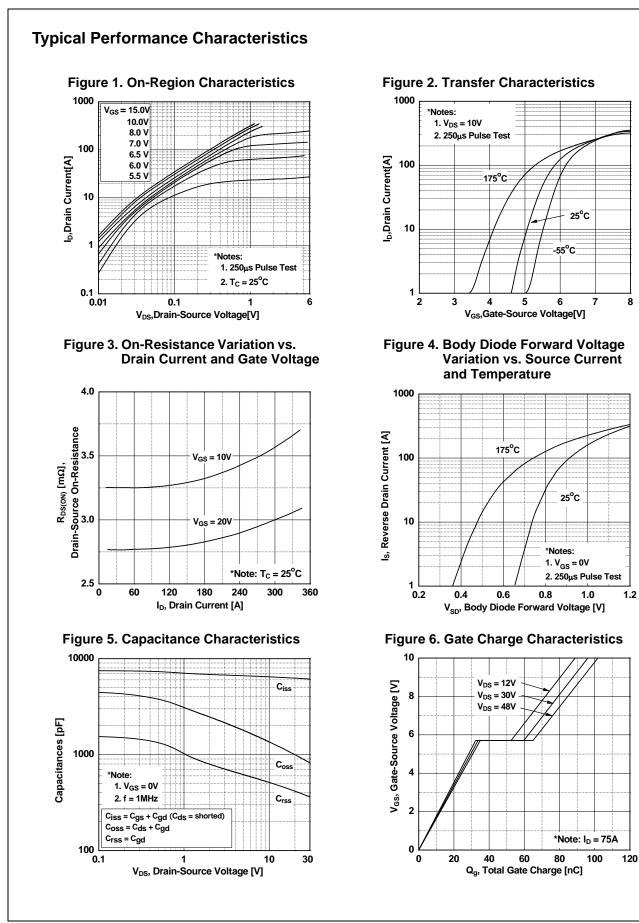
Notes:

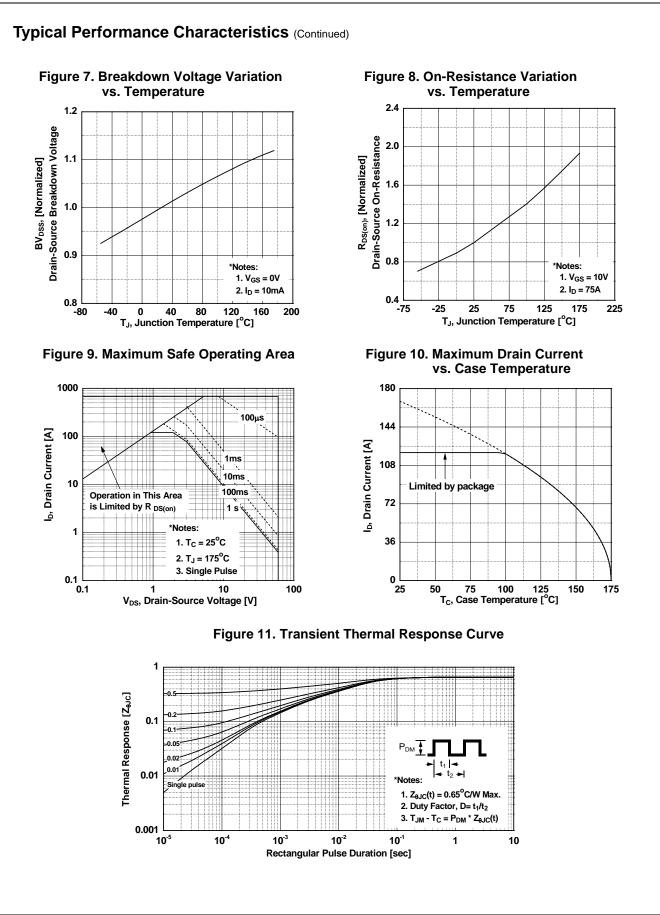
Notes: 1: Repetitive Rating: Pulse width limited by maximum junction temperature 2: L = 0.31mH, $I_{AS} = 75A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$ 3: $I_{SD} \le 75A$, di/dt $\le 200A/\mu$ s, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$ 4: Essentially Independent of Operating Temperature Typical Characteristics

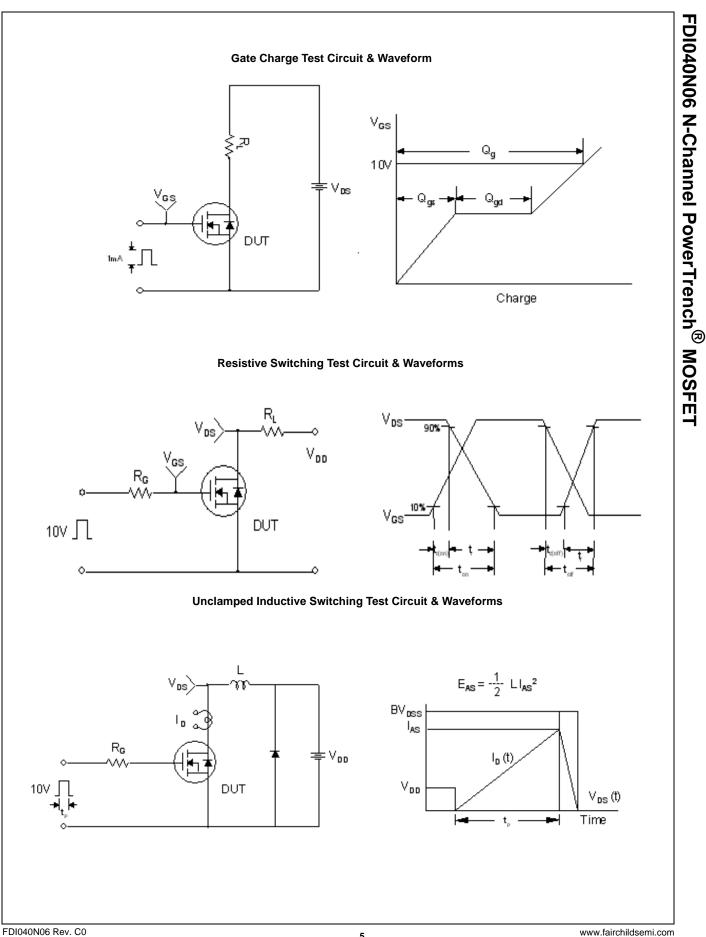
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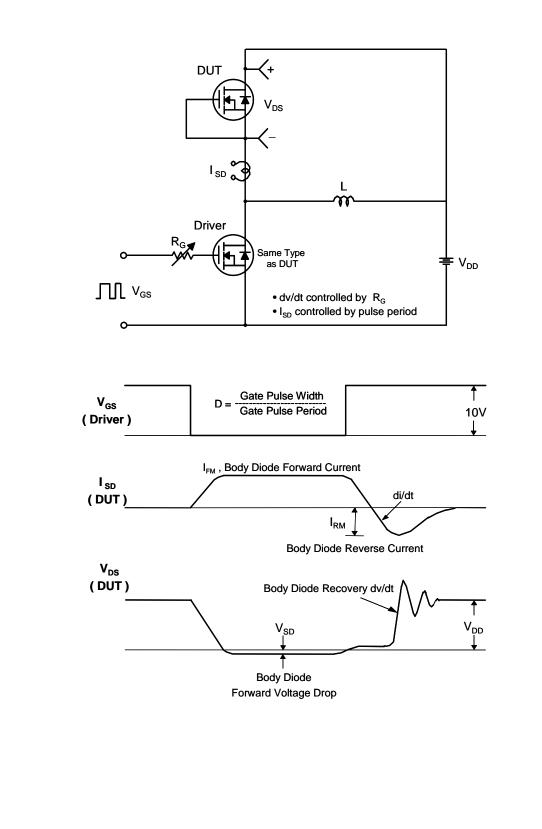
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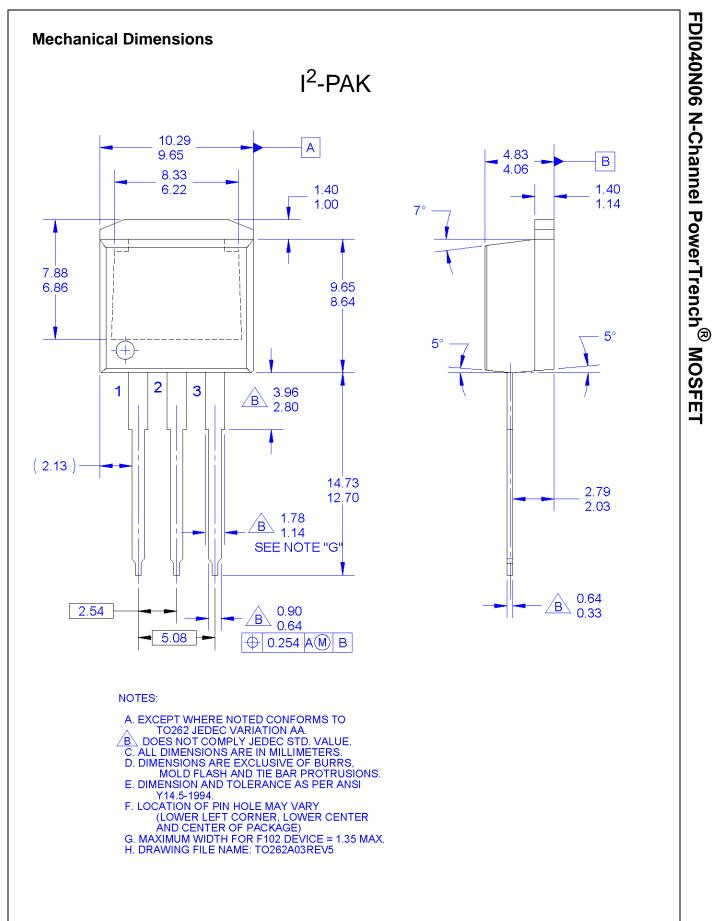


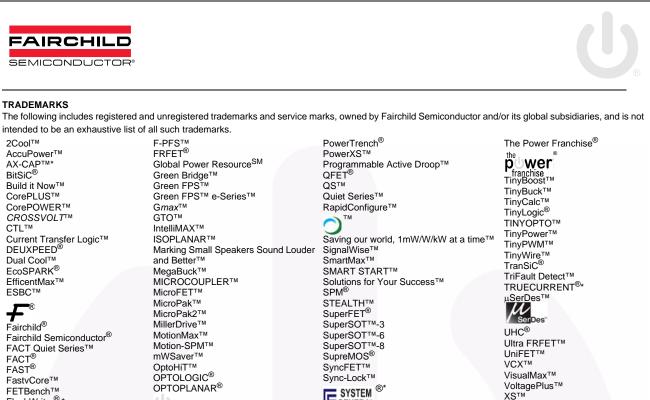




Peak Diode Recovery dv/dt Test Circuit & Waveforms







FastvCore™ FETBench™ FlashWriter[®] * FPS™

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